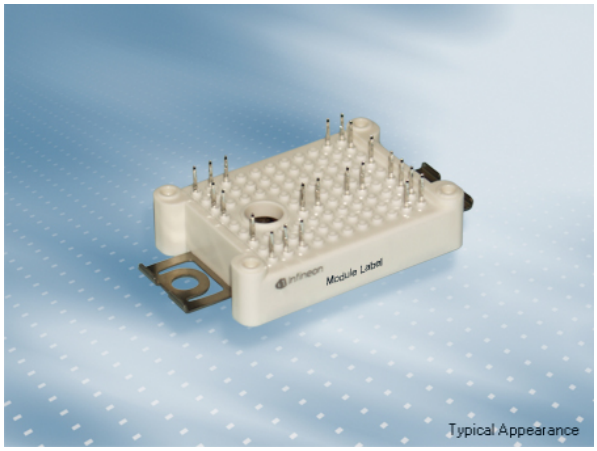
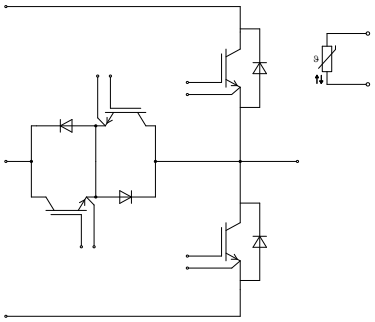
Technische Information / Technical Information

IGBT-Modul
IGBT-Module

F3L75R12W1H3_B27





V_{CES} = 1200V
$I_{C\ nom}$ = 75A / I_{CRM} = 150A

Typische Anwendungen

- 3-Level-Applikationen
- Solar Anwendungen

Typical Applications

- 3-level-applications
- Solar applications

Elektrische Eigenschaften

- High Speed IGBT H3
- Niederinduktives Design
- Niedrige Schaltverluste
- Niedriges V_{CEsat}

Electrical Features

- High speed IGBT H3
- Low inductive design
- Low switching losses
- Low V_{CEsat}

Mechanische Eigenschaften

- 3 kV AC 1min Isolationsfestigkeit
- Al_2O_3 Substrat mit kleinem thermischen Widerstand
- Kompaktes Design
- PressFIT Verbindungstechnik
- Robuste Montage durch integrierte Befestigungsklammern

Mechanical Features

- 3 kV AC 1min insulation
- Al_2O_3 substrate with low thermal resistance
- Compact design
- PressFIT contact technology
- Rugged mounting due to integrated mounting clamps

Module Label Code

Barcode Code 128

Sample
00000123456000000000000

DMX - Code

Content of the Code	Digit
Module Serial Number	1 - 5
Module Material Number	6 - 11
Production Order Number	12 - 19
Datecode (Production Year)	20 - 21
Datecode (Production Week)	22 - 23

prepared by: CM	date of publication: 2016-04-04	
approved by: AKDA	revision: V3.2	UL approved (E83335)

IGBT, T1-T4 / IGBT, T1-T4

Höchstzulässige Werte / Maximum Rated Values

Kollektor-Emitter-Sperrspannung Collector-emitter voltage	T_{vj} = 25°C	V_{CES}	1200	V
Implementierter Kollektor-Strom Implemented collector current		I_{CN}	75	A
Kollektor-Dauergleichstrom Continuous DC collector current	T_C = 100°C, $T_{vj\,max}$ = 175°C T_C = 25°C, $T_{vj\,max}$ = 175°C	$I_{C\,nom}$ I_C	30 45	A A
Periodischer Kollektor-Spitzenstrom Repetitive peak collector current	t_P = 1 ms	I_{CRM}	150	A
Gesamt-Verlustleistung Total power dissipation	T_C = 25°C, $T_{vj\,max}$ = 175°C	P_{tot}	275	W
Gate-Emitter-Spitzenspannung Gate-emitter peak voltage		V_{GES}	+/-20	V

Charakteristische Werte / Characteristic Values

			min.	typ.	max.	
Kollektor-Emitter-Sättigungsspannung Collector-emitter saturation voltage	I_C = 30 A, V_{GE} = 15 V I_C = 30 A, V_{GE} = 15 V I_C = 30 A, V_{GE} = 15 V	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	$V_{CE\,sat}$		1,45 1,55 1,60	1,70	V V V
Gate-Schwellenspannung Gate threshold voltage	I_C = 2,60 mA, V_{CE} = V_{GE}, T_{vj} = 25°C		V_{GEth}	5,00	5,80	6,50	V
Gateladung Gate charge	V_{GE} = -15 V ... +15 V		Q_G		0,57		µC
Interner Gatewiderstand Internal gate resistor	T_{vj} = 25°C		R_{Gint}		0,0		Ω
Eingangskapazität Input capacitance	f = 1 MHz, T_{vj} = 25°C, V_{CE} = 25 V, V_{GE} = 0 V		C_{ies}		4,40		nF
Rückwirkungskapazität Reverse transfer capacitance	f = 1 MHz, T_{vj} = 25°C, V_{CE} = 25 V, V_{GE} = 0 V		C_{res}		0,235		nF
Kollektor-Emitter-Reststrom Collector-emitter cut-off current	V_{CE} = 1200 V, V_{GE} = 0 V, T_{vj} = 25°C		I_{CES}			1,0	mA
Gate-Emitter-Reststrom Gate-emitter leakage current	V_{CE} = 0 V, V_{GE} = 20 V, T_{vj} = 25°C		I_{GES}			100	nA
Einschaltverzögerungszeit, induktive Last Turn-on delay time, inductive load	I_C = 30 A, V_{CE} = 400 V V_{GE} = 15 V R_{Gon} = 6,8 Ω	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	$t_{d\,on}$		0,03 0,03 0,03		µs µs µs
Anstiegszeit, induktive Last Rise time, inductive load	I_C = 30 A, V_{CE} = 400 V V_{GE} = 15 V R_{Gon} = 6,8 Ω	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	t_r		0,01 0,012 0,012		µs µs µs
Abschaltverzögerungszeit, induktive Last Turn-off delay time, inductive load	I_C = 30 A, V_{CE} = 400 V V_{GE} = 15 V R_{Goff} = 6,8 Ω	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	$t_{d\,off}$		0,25 0,32 0,34		µs µs µs
Fallzeit, induktive Last Fall time, inductive load	I_C = 30 A, V_{CE} = 400 V V_{GE} = 15 V R_{Goff} = 6,8 Ω	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	t_f		0,025 0,04 0,045		µs µs µs
Einschaltverlustenergie pro Puls Turn-on energy loss per pulse	I_C = 30 A, V_{CE} = 400 V, L_S = 40 nH V_{GE} = 15 V, di/dt = 2600 A/µs (T_{vj} = 150°C) R_{Gon} = 6,8 Ω	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	E_{on}		0,40 0,60 0,70		mJ mJ mJ
Abschaltverlustenergie pro Puls Turn-off energy loss per pulse	I_C = 30 A, V_{CE} = 400 V, L_S = 40 nH V_{GE} = 15 V, du/dt = 2400 V/µs (T_{vj} = 150°C) R_{Goff} = 6,8 Ω	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	E_{off}		1,05 1,60 1,75		mJ mJ mJ
Kurzschlußverhalten SC data	V_{GE} ≤ 15 V, V_{CC} = 800 V V_{CEmax} = V_{CES} -L_{sCE} ·di/dt	t_P ≤ 10 µs, T_{vj} = 150°C	I_{SC}		270		A
Wärmewiderstand, Chip bis Gehäuse Thermal resistance, junction to case	pro IGBT / per IGBT		R_{thJC}		0,500	0,550	K/W

Wärmewiderstand, Gehäuse bis Kühlkörper Thermal resistance, case to heatsink	pro IGBT / per IGBT λ_{Paste} = 1 W/(m·K) / λ_{grease} = 1 W/(m·K)	R_{thCH}		0,450		K/W
Temperatur im Schaltbetrieb Temperature under switching conditions		$T_{vj\,op}$	-40		150	°C

Diode, D1 / D4 / Diode, D1 / D4

Höchstzulässige Werte / Maximum Rated Values

Periodische Spitzensperrspannung Repetitive peak reverse voltage	T_{vj} = 25°C	V_{RRM}		1200		V
Dauergleichstrom Continuous DC forward current		I_F		30		A
Periodischer Spitzenstrom Repetitive peak forward current	t_P = 1 ms	I_{FRM}		50		A
Grenzlastintegral I²t - value	V_R = 0 V, t_P = 10 ms, T_{vj} = 125°C V_R = 0 V, t_P = 10 ms, T_{vj} = 150°C	I²t		90,0 75,0		A²s A²s

Charakteristische Werte / Characteristic Values

			min.	typ.	max.	
Durchlassspannung Forward voltage	I_F = 30 A, V_{GE} = 0 V I_F = 30 A, V_{GE} = 0 V I_F = 30 A, V_{GE} = 0 V	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	V_F		1,85 1,90 1,90	2,40	V V V
Rückstromspitze Peak reverse recovery current	I_F = 30 A, - di_F/dt = 2600 A/µs (T_{vj}=150°C) V_R = 400 V V_{GE} = -15 V	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	I_{RM}		72,0 80,0 82,0		A A A
Sperrverzögerungsladung Recovered charge	I_F = 30 A, - di_F/dt = 2600 A/µs (T_{vj}=150°C) V_R = 400 V V_{GE} = -15 V	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	Q_r		2,35 2,85 3,70		µC µC µC
Abschaltenergie pro Puls Reverse recovery energy	I_F = 30 A, - di_F/dt = 2600 A/µs (T_{vj}=150°C) V_R = 400 V V_{GE} = -15 V	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	E_{rec}		0,80 1,30 1,35		mJ mJ mJ
Wärmewiderstand, Chip bis Gehäuse Thermal resistance, junction to case	pro Diode / per diode		R_{thJC}		0,950	1,05	K/W
Wärmewiderstand, Gehäuse bis Kühlkörper Thermal resistance, case to heatsink	pro Diode / per diode λ_{Paste} = 1 W/(m·K) / λ_{grease} = 1 W/(m·K)		R_{thCH}		0,850		K/W
Temperatur im Schaltbetrieb Temperature under switching conditions			$T_{vj\,op}$	-40		150	°C

IGBT, T2 / T3 / IGBT, T2 / T3

Höchstzulässige Werte / Maximum Rated Values

Kollektor-Emitter-Sperrspannung Collector-emitter voltage	T_{vj} = 25°C	V_{CES}	650		V
Kollektor-Dauergleichstrom Continuous DC collector current	T_C = 80°C, $T_{vj\,max}$ = 175°C T_C = 25°C, $T_{vj\,max}$ = 175°C	$I_{C\,nom}$ I_C	30 45		A A
Periodischer Kollektor-Spitzenstrom Repetitive peak collector current	t_P = 1 ms	I_{CRM}	60		A
Gesamt-Verlustleistung Total power dissipation	T_C = 25°C, $T_{vj\,max}$ = 175°C	P_{tot}	150		W
Gate-Emitter-Spitzenspannung Gate-emitter peak voltage		V_{GES}	+/-20		V

Charakteristische Werte / Characteristic Values

			min.	typ.	max.	
Kollektor-Emitter-Sättigungsspannung Collector-emitter saturation voltage	I_C = 30 A, V_{GE} = 15 V, T_{vj} = 25°C I_C = 30 A, V_{GE} = 15 V, T_{vj} = 125°C I_C = 30 A, V_{GE} = 15 V, T_{vj} = 150°C	$V_{CE\,sat}$		1,55 1,70 1,80	2,00	V V V
Gate-Schwellenspannung Gate threshold voltage	I_C = 0,30 mA, V_{CE} = V_{GE}, T_{vj} = 25°C	V_{GEth}	4,90	5,80	6,50	V
Gateladung Gate charge	V_{GE} = -15 V ... +15 V	Q_G		0,30		µC
Interner Gatewiderstand Internal gate resistor	T_{vj} = 25°C	R_{Gint}		0,0		Ω
Eingangskapazität Input capacitance	f = 1 MHz, T_{vj} = 25°C, V_{CE} = 25 V, V_{GE} = 0 V	C_{ies}		1,65		nF
Rückwirkungskapazität Reverse transfer capacitance	f = 1 MHz, T_{vj} = 25°C, V_{CE} = 25 V, V_{GE} = 0 V	C_{res}		0,051		nF
Kollektor-Emitter-Reststrom Collector-emitter cut-off current	V_{CE} = 650 V, V_{GE} = 0 V, T_{vj} = 25°C	I_{CES}			1,0	mA
Gate-Emitter-Reststrom Gate-emitter leakage current	V_{CE} = 0 V, V_{GE} = 20 V, T_{vj} = 25°C	I_{GES}			100	nA
Einschaltverzögerungszeit, induktive Last Turn-on delay time, inductive load	I_C = 30 A, V_{CE} = 400 V, T_{vj} = 25°C V_{GE} = 15 V, T_{vj} = 125°C R_{Gon} = 10 Ω, T_{vj} = 150°C	$t_{d\,on}$		0,022 0,025 0,025		µs µs µs
Anstiegszeit, induktive Last Rise time, inductive load	I_C = 30 A, V_{CE} = 400 V, T_{vj} = 25°C V_{GE} = 15 V, T_{vj} = 125°C R_{Gon} = 10 Ω, T_{vj} = 150°C	t_r		0,01 0,012 0,012		µs µs µs
Abschaltverzögerungszeit, induktive Last Turn-off delay time, inductive load	I_C = 30 A, V_{CE} = 400 V, T_{vj} = 25°C V_{GE} = 15 V, T_{vj} = 125°C R_{Goff} = 10 Ω, T_{vj} = 150°C	$t_{d\,off}$		0,16 0,18 0,185		µs µs µs
Fallzeit, induktive Last Fall time, inductive load	I_C = 30 A, V_{CE} = 400 V, T_{vj} = 25°C V_{GE} = 15 V, T_{vj} = 125°C R_{Goff} = 10 Ω, T_{vj} = 150°C	t_f		0,025 0,037 0,04		µs µs µs
Einschaltverlustenergie pro Puls Turn-on energy loss per pulse	I_C = 30 A, V_{CE} = 400 V, L_S = 40 nH, T_{vj} = 25°C V_{GE} = 15 V, di/dt = 2600 A/µs (T_{vj} = 150°C), T_{vj} = 125°C R_{Gon} = 10 Ω, T_{vj} = 150°C	E_{on}		0,34 0,50 0,53		mJ mJ mJ
Abschaltverlustenergie pro Puls Turn-off energy loss per pulse	I_C = 30 A, V_{CE} = 400 V, L_S = 40 nH, T_{vj} = 25°C V_{GE} = 15 V, du/dt = 4700 V/µs (T_{vj} = 150°C), T_{vj} = 125°C R_{Goff} = 10 Ω, T_{vj} = 150°C	E_{off}		0,85 1,15 1,20		mJ mJ mJ
Kurzschlußverhalten SC data	V_{GE} ≤ 15 V, V_{CC} = 360 V, t_P ≤ 8 µs, T_{vj} = 25°C V_{CEmax} = V_{CES} -L_{sCE} ·di/dt, t_P ≤ 6 µs, T_{vj} = 150°C	I_{SC}		210 150		A A
Wärmewiderstand, Chip bis Gehäuse Thermal resistance, junction to case	pro IGBT / per IGBT	R_{thJC}		0,900	1,00	K/W
Wärmewiderstand, Gehäuse bis Kühlkörper Thermal resistance, case to heatsink	pro IGBT / per IGBT λ_{Paste} = 1 W/(m·K) / λ_{grease} = 1 W/(m·K)	R_{thCH}		0,850		K/W
Temperatur im Schaltbetrieb Temperature under switching conditions		$T_{vj\,op}$	-40		150	°C

prepared by: CM	date of publication: 2016-04-04
approved by: AKDA	revision: V3.2

Diode, D2 / D3 / Diode, D2 / D3

Höchstzulässige Werte / Maximum Rated Values

Periodische Spitzensperrspannung Repetitive peak reverse voltage	T_{vj} = 25°C	V_{RRM}	650	V
Dauergleichstrom Continuous DC forward current		I_F	30	A
Periodischer Spitzenstrom Repetitive peak forward current	t_P = 1 ms	I_{FRM}	60	A
Grenzlastintegral I²t - value	V_R = 0 V, t_P = 10 ms, T_{vj} = 125°C V_R = 0 V, t_P = 10 ms, T_{vj} = 150°C	I²t	130 115	A²s A²s

Charakteristische Werte / Characteristic Values

			min.	typ.	max.	
Durchlassspannung Forward voltage	I_F = 30 A, V_{GE} = 0 V I_F = 30 A, V_{GE} = 0 V I_F = 30 A, V_{GE} = 0 V	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	V_F		1,45 1,35 1,30	1,65	V V V
Rückstromspitze Peak reverse recovery current	I_F = 30 A, - di_F/dt = 2600 A/µs (T_{vj}=150°C) V_R = 400 V	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	I_{RM}		42,0 48,0 50,0		A A A
Sperrverzögerungsladung Recovered charge	I_F = 30 A, - di_F/dt = 2600 A/µs (T_{vj}=150°C) V_R = 400 V	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	Q_r		1,80 2,40 2,60		µC µC µC
Abschaltenergie pro Puls Reverse recovery energy	I_F = 30 A, - di_F/dt = 2600 A/µs (T_{vj}=150°C) V_R = 400 V	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	E_{rec}		0,45 0,65 0,73		mJ mJ mJ
Wärmewiderstand, Chip bis Gehäuse Thermal resistance, junction to case	pro Diode / per diode		R_{thJC}		1,00	1,20	K/W
Wärmewiderstand, Gehäuse bis Kühlkörper Thermal resistance, case to heatsink	pro Diode / per diode λ_{Paste} = 1 W/(m·K) / λ_{grease} = 1 W/(m·K)		R_{thCH}		0,700		K/W
Temperatur im Schaltbetrieb Temperature under switching conditions			$T_{vj\,op}$	-40		150	°C

NTC-Widerstand / NTC-Thermistor

Charakteristische Werte / Characteristic Values

			min.	typ.	max.	
Nennwiderstand Rated resistance	T_{NTC} = 25°C	R_{25}		5,00		kΩ
Abweichung von R100 Deviation of R100	T_{NTC} = 100°C, R_{100} = 493 Ω	ΔR/R	-5		5	%
Verlustleistung Power dissipation	T_{NTC} = 25°C	P_{25}			20,0	mW
B-Wert B-value	$R_2 = R_{25} \exp [B_{25/50}(1/T_2 - 1/(298{,}15\ K))]$	$B_{25/50}$		3375		K
B-Wert B-value	$R_2 = R_{25} \exp [B_{25/80}(1/T_2 - 1/(298{,}15\ K))]$	$B_{25/80}$		3411		K
B-Wert B-value	$R_2 = R_{25} \exp [B_{25/100}(1/T_2 - 1/(298{,}15\ K))]$	$B_{25/100}$		3433		K

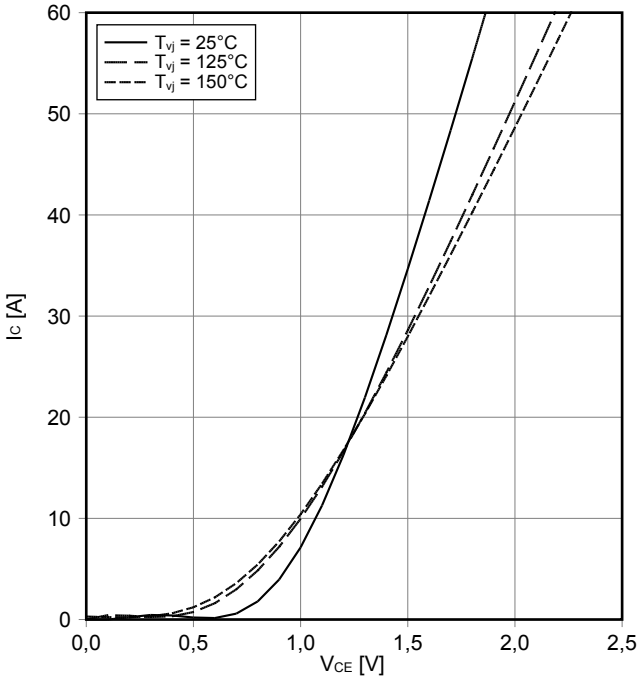
Angaben gemäß gültiger Application Note.
Specification according to the valid application note.

Modul / Module

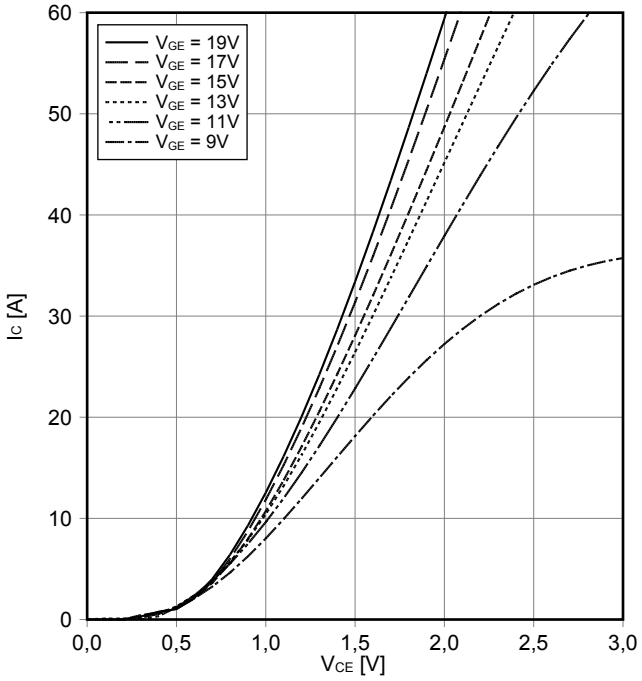
Isolations-Prüfspannung Isolation test voltage	RMS, f = 50 Hz, t = 1 min.	V_{ISOL}		3,0		kV
Innere Isolation Internal isolation	Basisisolierung (Schutzklasse 1, EN61140) basic insulation (class 1, IEC 61140)			Al_2O_3		
Kriechstrecke Creepage distance	Kontakt - Kühlkörper / terminal to heatsink Kontakt - Kontakt / terminal to terminal			11,5 6,3		mm
Luftstrecke Clearance	Kontakt - Kühlkörper / terminal to heatsink Kontakt - Kontakt / terminal to terminal			10,0 5,0		mm
Vergleichszahl der Kriechwegbildung Comperative tracking index		CTI		> 200		
			min.	typ.	max.	
Modulstreuinduktivität Stray inductance module		L_{sCE}		30		nH
Modulleitungswiderstand, Anschlüsse - Chip Module lead resistance, terminals - chip	T_C = 25°C, pro Schalter / per switch	$R_{CC'+EE'}$ $R_{AA'+CC'}$		5,00 6,00		mΩ
Lagertemperatur Storage temperature		T_{stg}	-40		125	°C
Anpresskraft für mech. Bef. pro Feder mountig force per clamp		F	40	-	80	N
Gewicht Weight		G		24		g

Der Strom im Dauerbetrieb ist auf 25A effektiv pro Anschlusspin begrenzt.
The current under continuous operation is limited to 25A rms per connector pin.

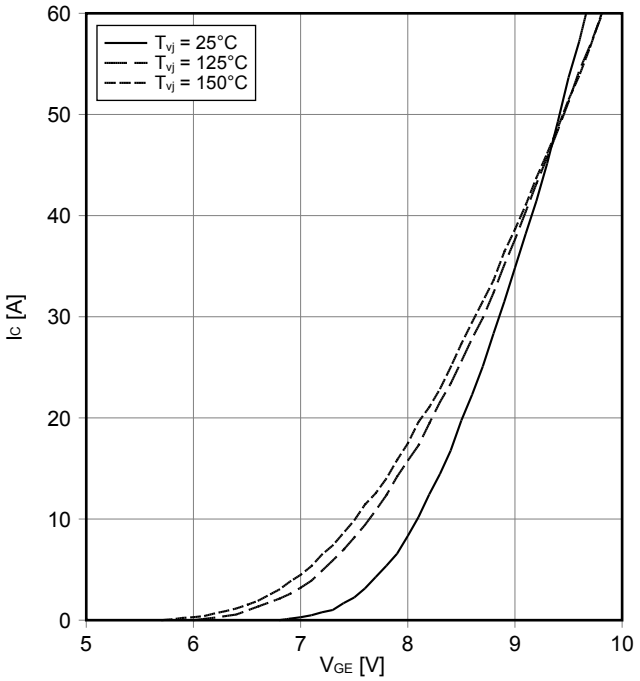
Ausgangskennlinie IGBT, T1-T4 (typisch)
output characteristic IGBT, T1-T4 (typical)
$I_C = f(V_{CE})$
V_{GE} = 15 V



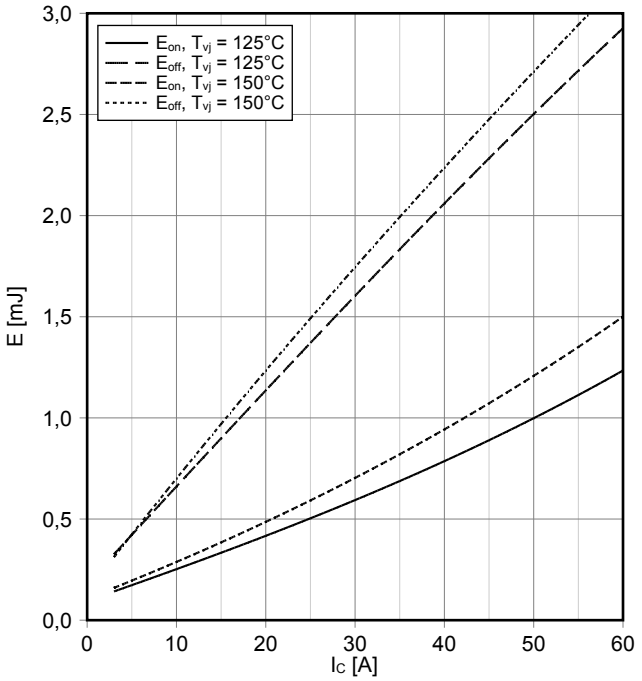
Ausgangskennlinienfeld IGBT, T1-T4 (typisch)
output characteristic IGBT, T1-T4 (typical)
$I_C = f(V_{CE})$
T_{vj} = 150°C



Übertragungscharakteristik IGBT, T1-T4 (typisch)
transfer characteristic IGBT, T1-T4 (typical)
$I_C = f(V_{GE})$
V_{CE} = 20 V

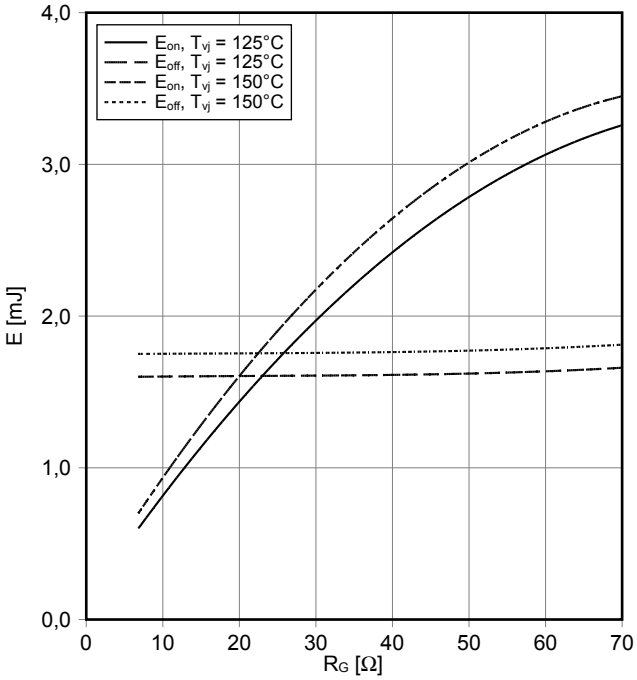


Schaltverluste IGBT, T1-T4 (typisch)
switching losses IGBT, T1-T4 (typical)
$E_{on} = f(I_C)$, $E_{off} = f(I_C)$
V_{GE} = ±15 V, R_{Gon} = 6.8 Ω, R_{Goff} = 6.8 Ω, V_{CE} = 400 V

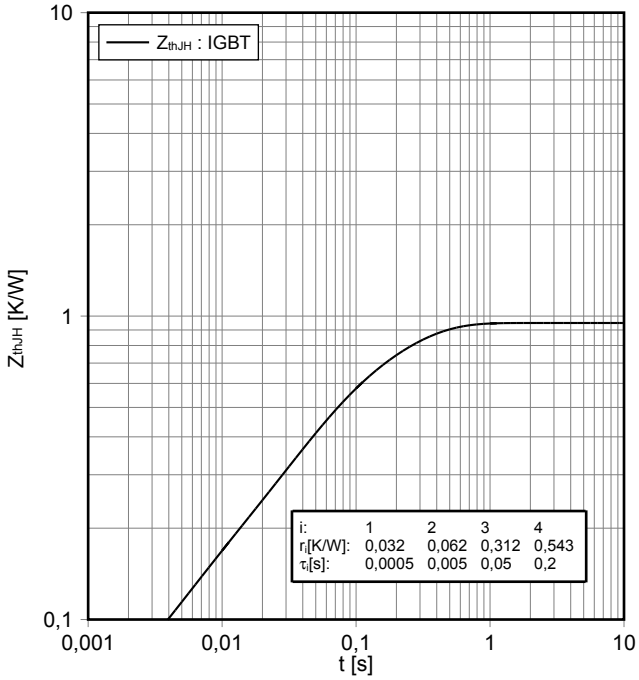


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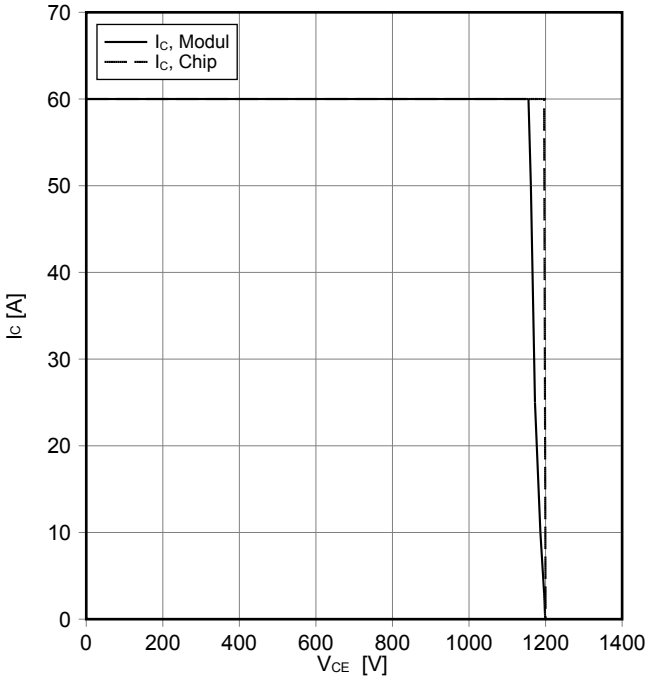
Schaltverluste IGBT, T1-T4 (typisch)
switching losses IGBT, T1-T4 (typical)
$E_{on} = f(R_G)$, $E_{off} = f(R_G)$
V_{GE} = ±15 V, I_C = 30 A, V_{CE} = 400 V



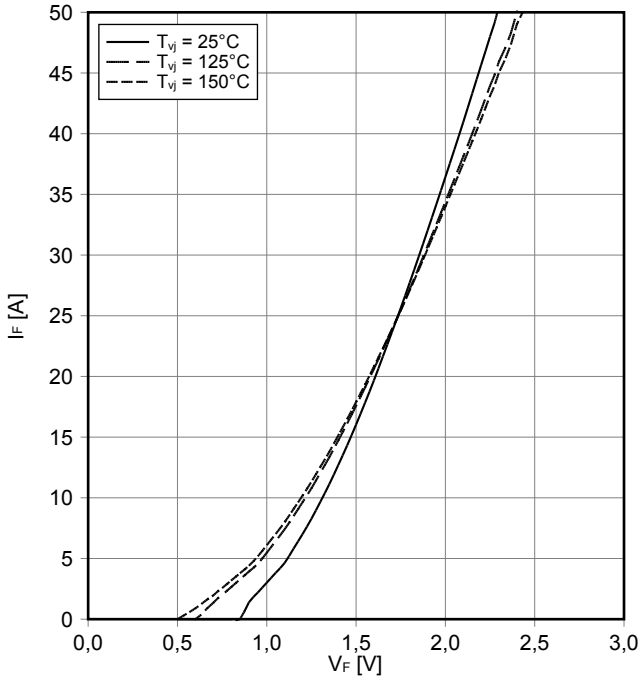
Transienter Wärmewiderstand IGBT, T1-T4
transient thermal impedance IGBT, T1-T4
$Z_{thJH} = f(t)$



Sicherer Rückwärts-Arbeitsbereich IGBT, T1-T4 (RBSOA)
reverse bias safe operating area IGBT, T1-T4 (RBSOA)
$I_C = f(V_{CE})$
V_{GE} = ±15 V, R_{Goff} = 6.8 Ω, T_{vj} = 150°C

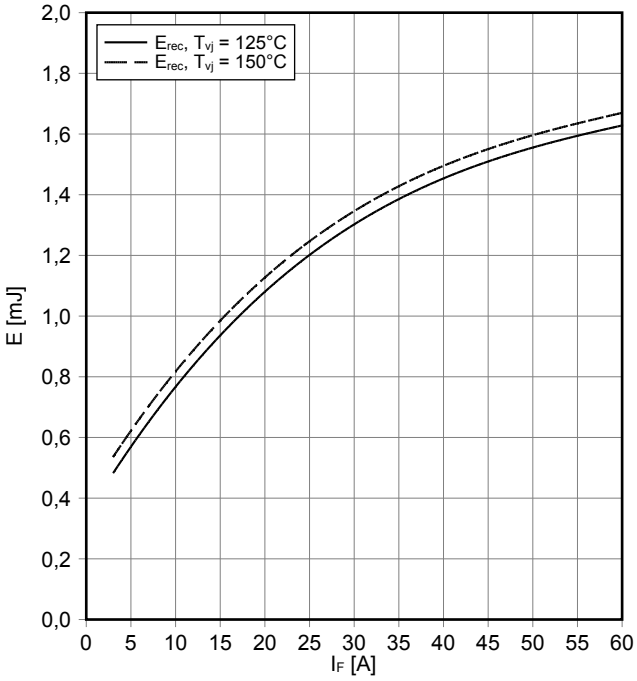


Durchlasskennlinie der Diode, D1 / D4 (typisch)
forward characteristic of Diode, D1 / D4 (typical)
$I_F = f(V_F)$

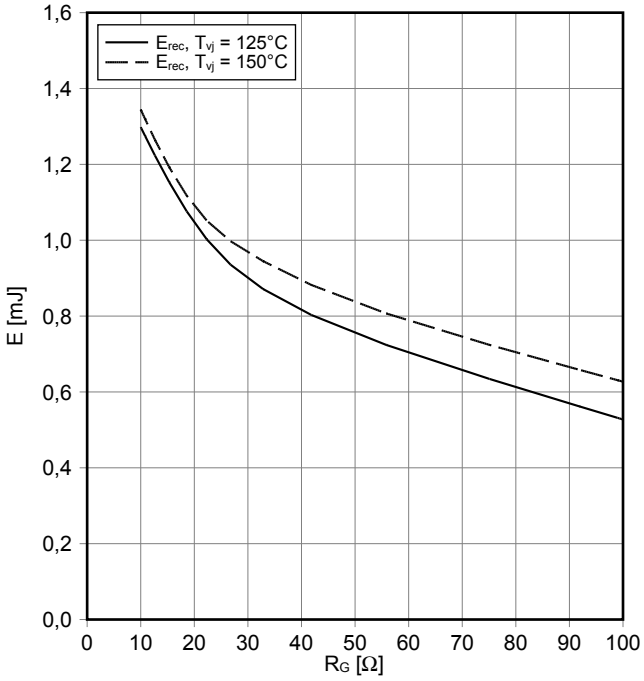


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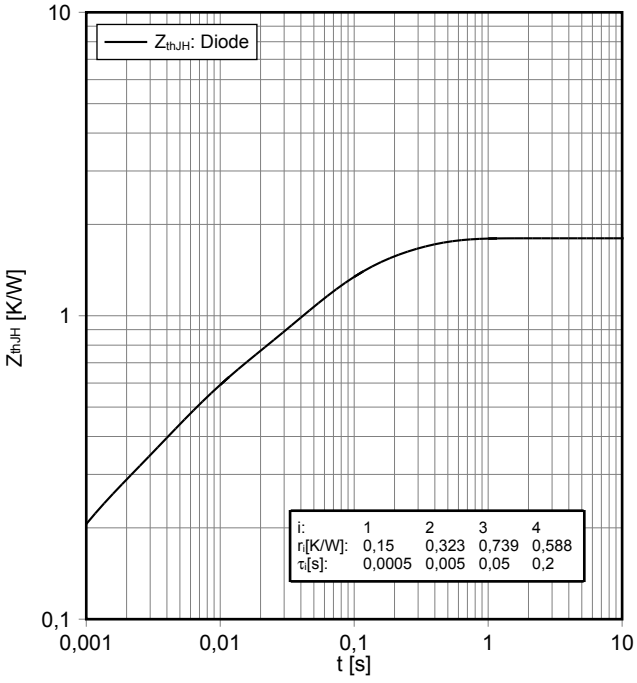
Schaltverluste Diode, D1 / D4 (typisch)
switching losses Diode, D1 / D4 (typical)
$E_{rec} = f(I_F)$
$R_{Gon} = 10\ \Omega$, $V_{CE} = 400$ V



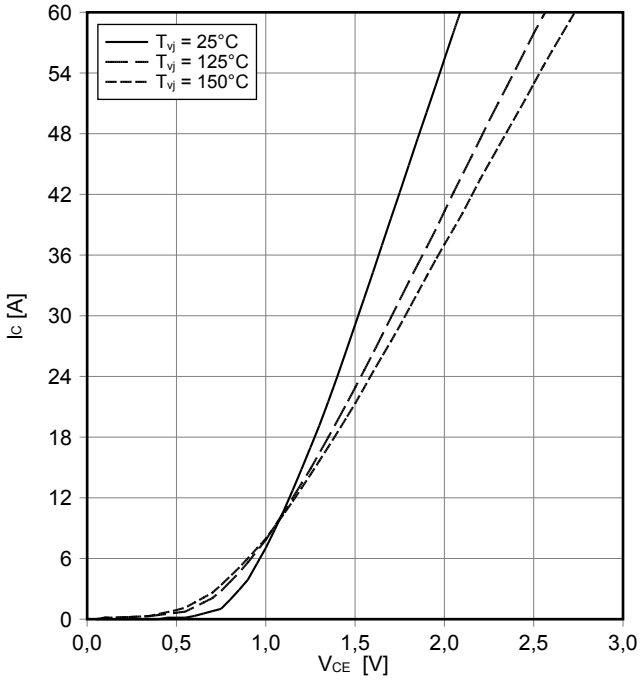
Schaltverluste Diode, D1 / D4 (typisch)
switching losses Diode, D1 / D4 (typical)
$E_{rec} = f(R_G)$
$I_F = 30$ A, $V_{CE} = 400$ V



Transienter Wärmewiderstand Diode, D1 / D4
transient thermal impedance Diode, D1 / D4
$Z_{thJH} = f(t)$

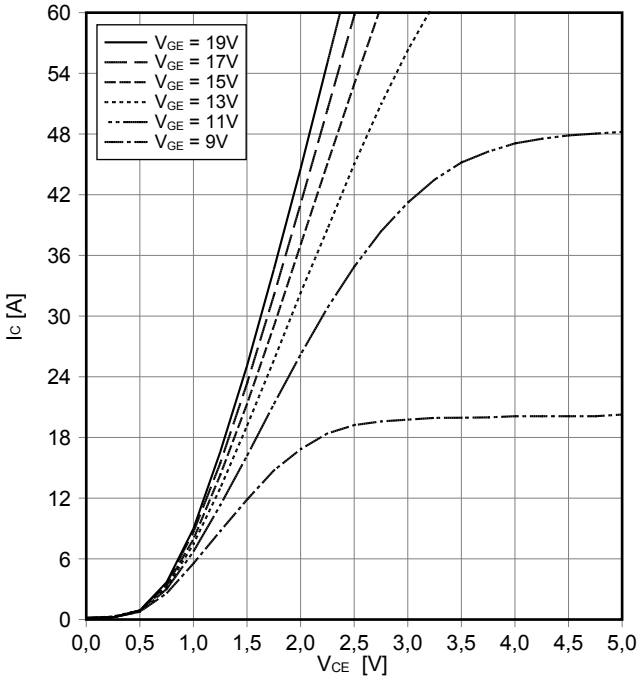


Ausgangskennlinie IGBT, T2 / T3 (typisch)
output characteristic IGBT, T2 / T3 (typical)
$I_C = f(V_{CE})$
$V_{GE} = 15$ V

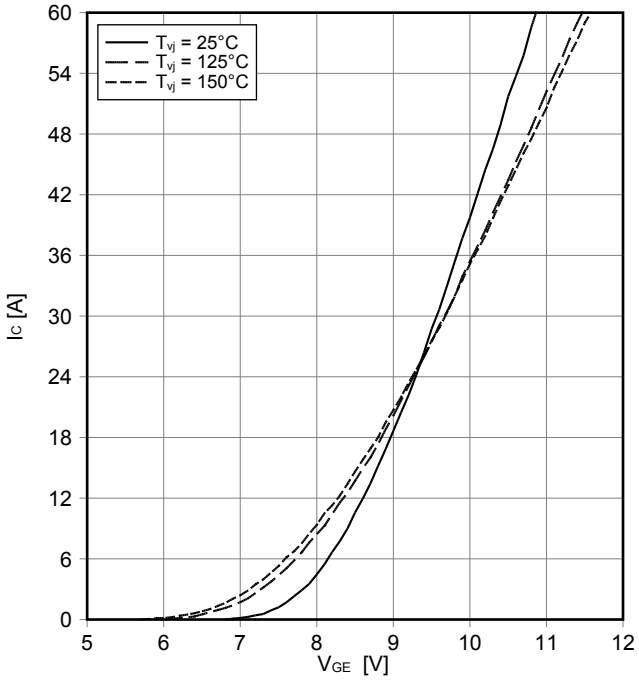


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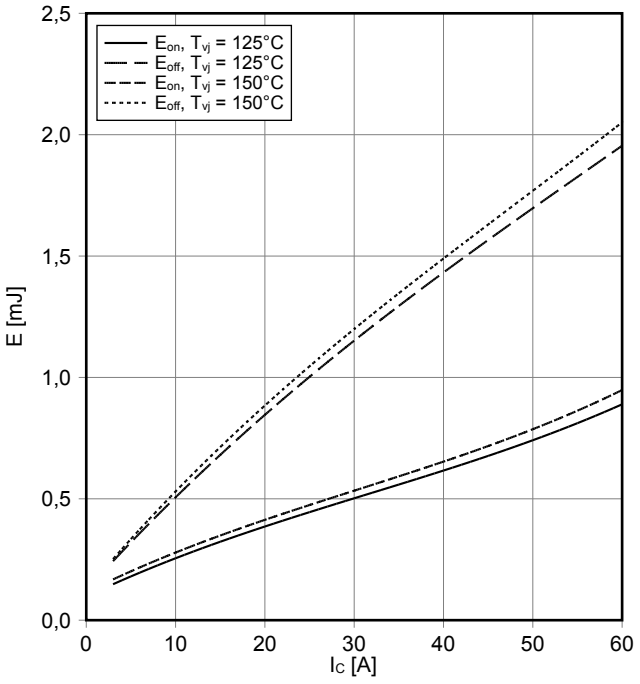
Ausgangskennlinienfeld IGBT, T2 / T3 (typisch)
output characteristic IGBT, T2 / T3 (typical)
$I_C = f(V_{CE})$
$T_{vj} = 150°C$



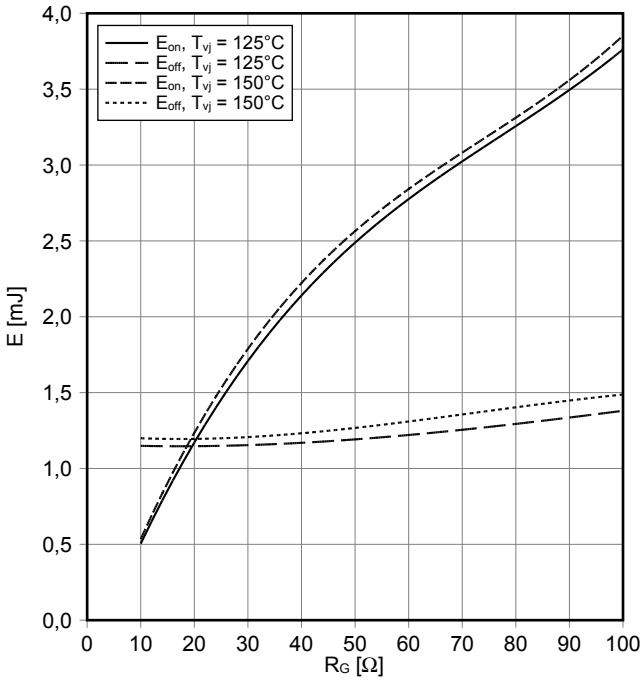
Übertragungscharakteristik IGBT, T2 / T3 (typisch)
transfer characteristic IGBT, T2 / T3 (typical)
$I_C = f(V_{GE})$
$V_{CE} = 20$ V



Schaltverluste IGBT, T2 / T3 (typisch)
switching losses IGBT, T2 / T3 (typical)
$E_{on} = f(I_C)$, $E_{off} = f(I_C)$
$V_{GE} = \pm 15$ V, $R_{Gon} = 10\ \Omega$, $R_{Goff} = 10\ \Omega$, $V_{CE} = 400$ V

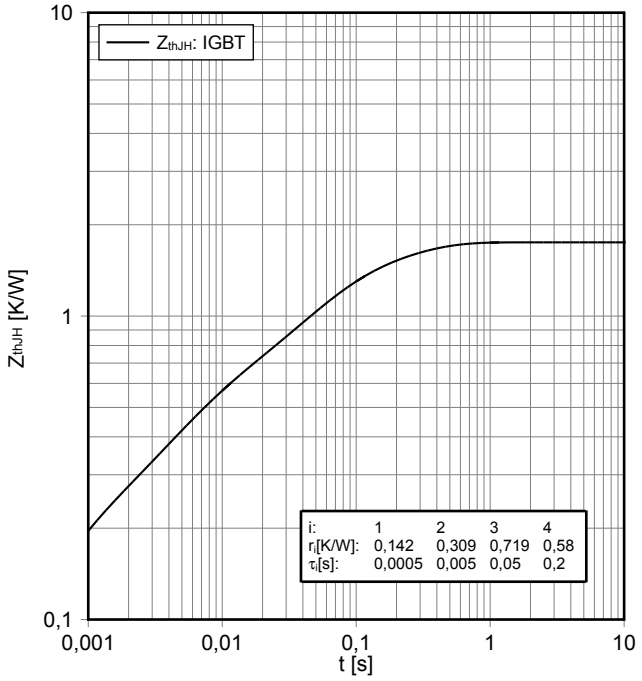


Schaltverluste IGBT, T2 / T3 (typisch)
switching losses IGBT, T2 / T3 (typical)
$E_{on} = f(R_G)$, $E_{off} = f(R_G)$
$V_{GE} = \pm 15$ V, $I_C = 30$ A, $V_{CE} = 400$ V

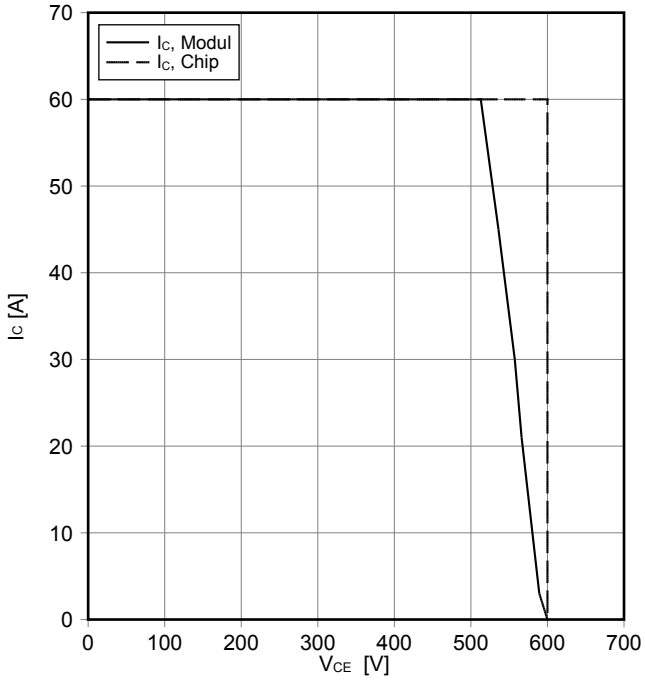


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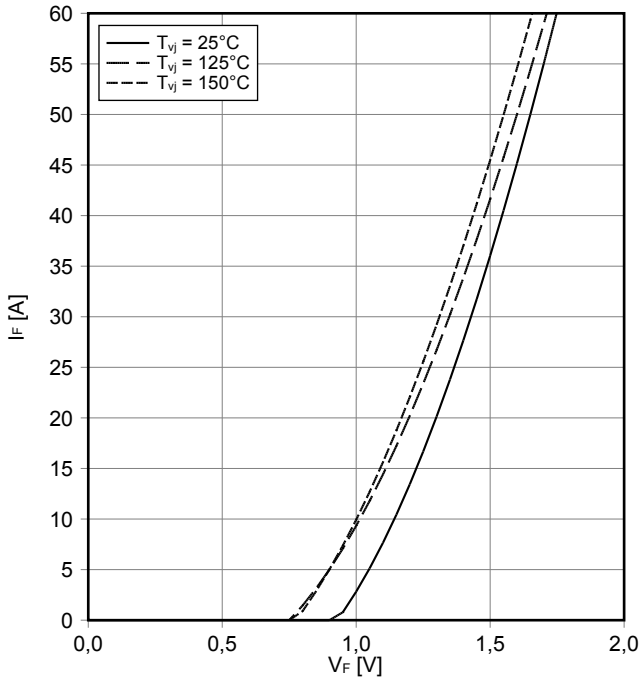
Transienter Wärmewiderstand IGBT, T2 / T3
transient thermal impedance IGBT, T2 / T3
$Z_{thJH} = f(t)$



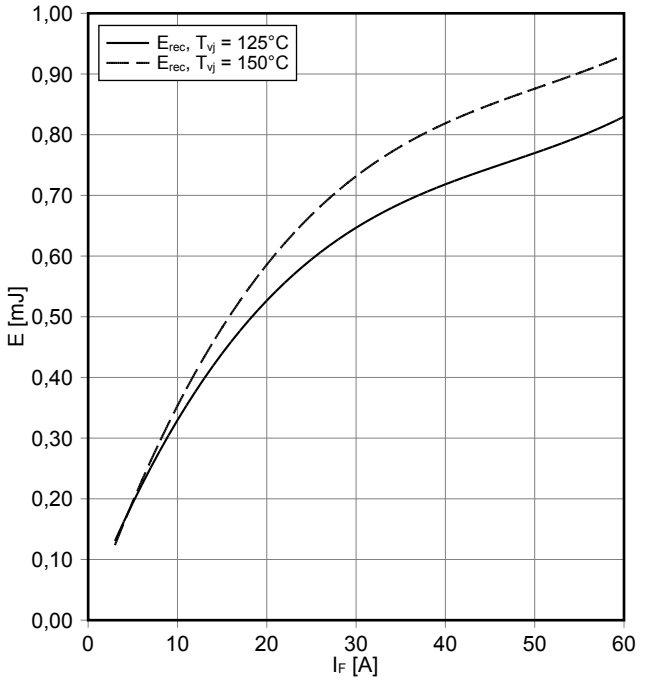
Sicherer Rückwärts-Arbeitsbereich IGBT, T2 / T3 (RBSOA)
reverse bias safe operating area IGBT, T2 / T3 (RBSOA)
$I_C = f(V_{CE})$
$V_{GE} = \pm 15$ V, $R_{Goff} = 10\ \Omega$, $T_{vj} = 150°C$



Durchlasskennlinie der Diode, D2 / D3 (typisch)
forward characteristic of Diode, D2 / D3 (typical)
$I_F = f(V_F)$

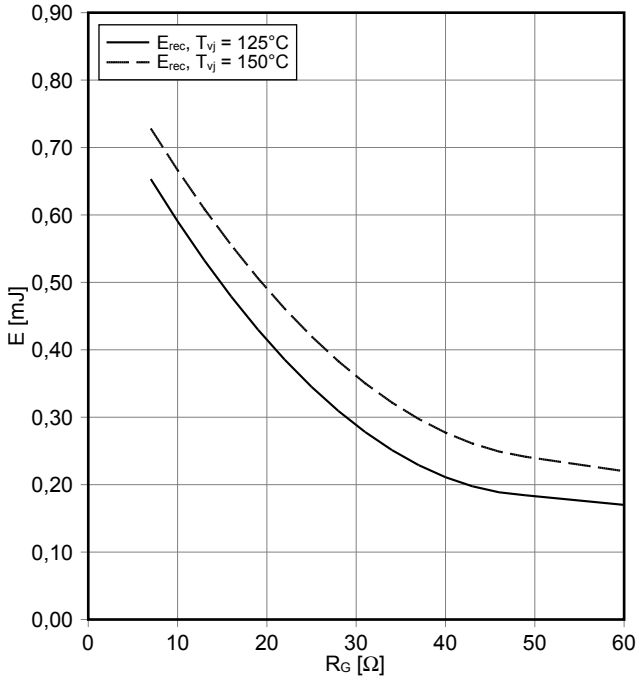


Schaltverluste Diode, D2 / D3 (typisch)
switching losses Diode, D2 / D3 (typical)
$E_{rec} = f(I_F)$
$R_{Gon} = 6.8\ \Omega$, $V_{CE} = 400$ V

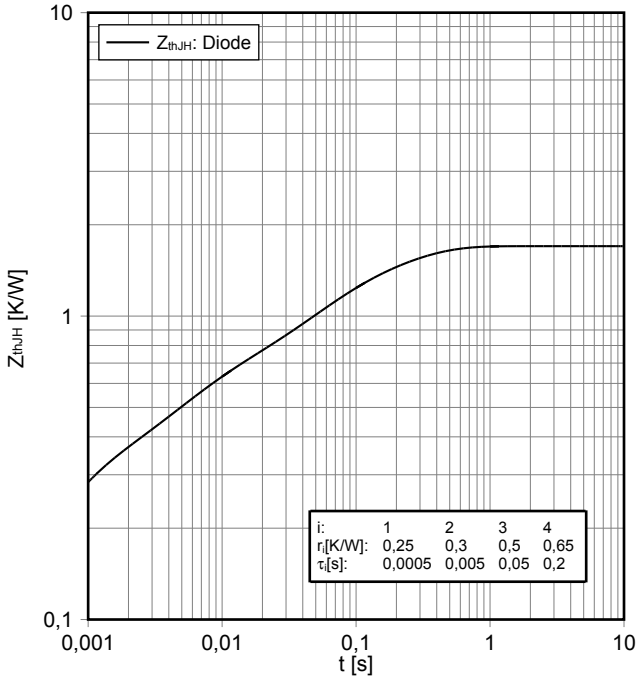


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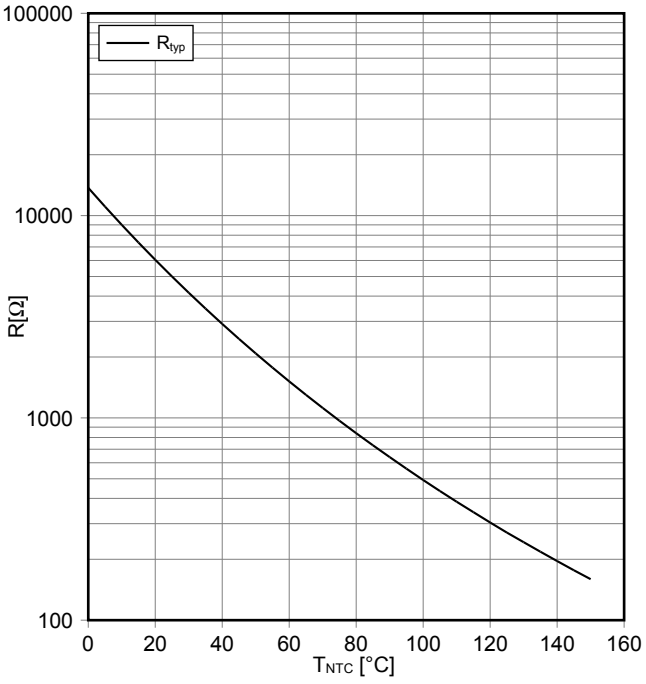
Schaltverluste Diode, D2 / D3 (typisch)
switching losses Diode, D2 / D3 (typical)
$E_{rec} = f(R_G)$
$I_F = 30\ A$, $V_{CE} = 400\ V$



Transienter Wärmewiderstand Diode, D2 / D3
transient thermal impedance Diode, D2 / D3
$Z_{thJH} = f(t)$

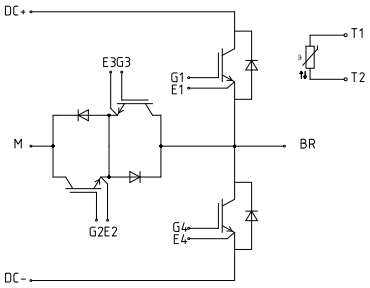


NTC-Widerstand-Temperaturkennlinie (typisch)
NTC-Thermistor-temperature characteristic (typical)
R = f (T)

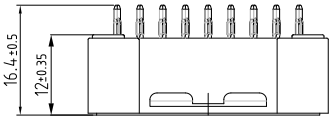


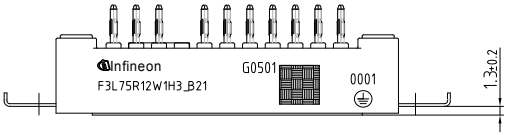
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Schaltplan / Circuit diagram

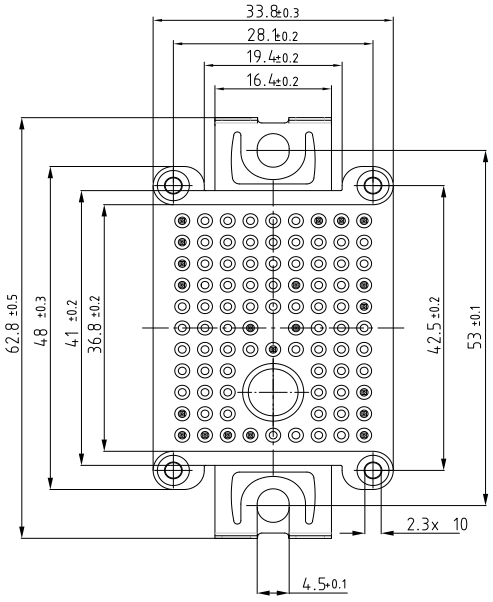


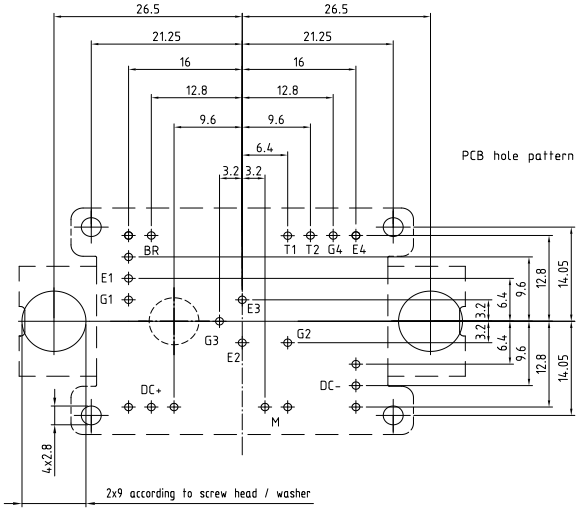
Gehäuseabmessungen / Package outlines





- Pin-Grid 3.2mm
- Tolerance of PCB hole pattern ⌖ ⌀0.1
- Hole specification for contacts see AN 2009-01
- Diameters of drill ⌀ 1.15mm
  and copper thickness in hole 25-50µm





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